L Number	Hits	Search Text	DB	Time stamp
2	1136	430/30.ccls.	USPAT	2004/09/08 15:49
5	706	(((356/$).CCLS.) and ((index near4 refract$3) or (refract$3 adj index))) and (grating and (wafer or semiconductor))	USPAT	2004/09/08 15:50
6	486	((((356/$).CCLS.) and ((index near4 refract$3) or (refract$3 adj index))) and (grating and (wafer or semiconductor))) and (liquid or medium or solution or bath)	USPAT	2004/09/08 15:51
7	4	(((((356/$).CCLS.) and ((index near4 refract$3) or (refract$3 adj index))) and (grating and (wafer or semiconductor))) and (liquid or medium or solution or bath)) and (immersion with (lithography or medium))	USPAT	2004/09/08 15:58
8	92	((((((356/$).CCLS.) and ((index near4 refract$3) or (refract$3 adj index))) and (grating and (wafer or semiconductor))) and (liquid or medium or solution or bath)) and lithography	USPAT	2004/09/08 15:59
9	988	438/5.ccls. or 438/7.ccls. or 438/16.ccls.	USPAT	2004/09/08 16:43
10	5	immersion adj lithography	USPAT	2004/09/08 17:38
11	0	((356/$).CCLS.) and (immersion adj lithography)	USPAT	2004/09/08 17:00
12	77	((356/$).CCLS.) and (lithography with (water or liquid or vapor or medium or solution or bath))	USPAT	2004/09/08 17:01
13	23	immersion adj lithography	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/08 17:38